MC10H116

Triple Line Receiver

Description

The MC10H116 is a triple differential amplifier designed for use in sensing differential signals over long lines and is a functional/pinout duplication of the MC10116, with 100% improvement in propagation delay and no increase in power supply current. For termination information see <u>AND8020</u>.

Features

- Propagation Delay, 1.0 ns Typical
- Power Dissipation 85 mW Typ/Pkg (same as MECL 10KTM)
- Improved Noise Margin 150 mV (Over Operating Voltage and Temperature Range)
- Voltage Compensated

pin with bubble goes

- MECL 10K Compatible
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

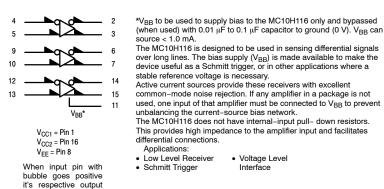
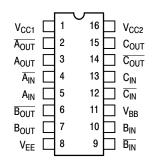


Figure 1. Logic Diagram



Pin assignment is for Dual-in-Line Package. For PLCC pin assignment, see TND309, the Pin Conversion Tables, page 9.

Figure 2. Dip Pin Assignment



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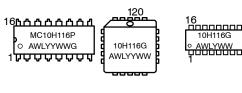






PDIP-16 P SUFFIX CASE 648-08 PLCC-20 FN SUFFIX CASE 775-02 SOIC-16 D SUFFIX CASE 751B-05

MARKING DIAGRAMS*



A = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10H116DG	SOIC-16 (Pb-Free)	48 Units/Tube
MC10H116DR2G	SOIC-16 (Pb-Free)	2500/Tape & Reel
MC10H116FNG	PLCC-20 (Pb-Free)	46 Units/Tube
MC10H116FNR2G	PLCC-20 (Pb-Free)	500/Tape & Reel
MC10H116PG	PDIP-16 (Pb-Free)	25 Units/Tube

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional marking information, refer to Application Note <u>AND8002/D</u>.

MC10H116

Table 1. MAXIMUM RATINGS

Symbol	Characteristic	Rating	Unit
V _{EE}	Power Supply (V _{CC} = 0)	-8.0 to 0	Vdc
VI	Input Voltage (V _{CC} = 0)	0 to V _{EE}	Vdc
I _{out}	Output Current Continuous Surge	50 100	mA
T _A	Operating Temperature Range	0 to +75	°C
T _{stg}	Storage Temperature Range Plastic Ceramic	–55 to +150 –55 to +165	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 2. ELECTRICAL CHARACTERISTICS (V_{EE} = -5.2 V ±5%) (Note 2)

		0 °		25 °		75°		
Symbol	Characteristic	Min	Max	Min	Max	Min	Max	Unit
Ι _Ε	Power Supply Current	-	23	_	21	_	23	mA
I _{inH}	Input Current High	_	150	_	95	-	95	μΑ
I _{CBO}	Input Leakage Current	_	1.5	_	1.0	-	1.0	μΑ
V _{BB}	Reference Voltage	-1.38	-1.27	-1.35	-1.25	-1.31	-1.19	Vdc
V _{OH}	High Output Voltage	-1.02	-0.84	-0.98	-0.81	-0.92	-0.735	Vdc
V _{OL}	Low Output Voltage	-1.95	-1.63	-1.95	-1.63	-1.95	-1.60	Vdc
V _{IH}	High Input Voltage (Note 1)	-1.17	-0.84	-0.84 -1.13 -0.81		-1.07	-0.735	Vdc
V _{IL}	Low Input Voltage (Note 1)	-1.95	-1.48	8 –1.95 –1.48 –1.		-1.95	-1.45	Vdc
V_{CMR}	Common Mode Range (Note 4)	_	_	-2.85 to -0.8		_	Vdc	
V_{PP}	Input Sensitivity (Note 3)	_	-	150	typ	_	_	mV_{PP}

^{1.} When $\ensuremath{V_{BB}}$ is used as the reference voltage.

Table 3. AC CHARACTERISTICS

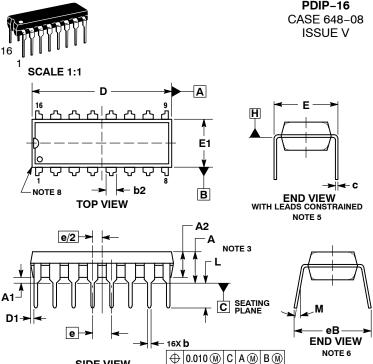
		0 °		25°		75°		
Symbol	Characteristic	Min	Max	Min	Max	Min	Max	Unit
t _{pd}	Propagation Delay	0.4	1.3	0.4	1.3	0.45	1.45	ns
t _r	Rise Time	0.5	1.5	0.5	1.6	0.5	1.7	ns
t _f	Fall Time	0.5	1.5	0.5	1.6	0.5	1.7	ns

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

^{2.} Each MECL 10H™ series circuit has been designed to meet the specifications shown in the test table, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 500 lfpm is maintained. Outputs are terminated through a 50 ohm resistor to −2.0 V.

^{3.} Differential input not to exceed 1.0 Vdc.

^{4.} 150 mV_{p-p} differential input required to obtain full logic swing on output.



PDIP-16

DATE 22 APR 2015

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

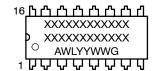
- DIMENSIONING AND TOLERANGING FER ASME 114-3M, 1994
 CONTROLLING DIMENSION: INCHES.

 DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.

 DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH
 OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
 NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- DIMENSION 8B IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
 DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
 PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100 BSC		2.54	BSC
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

= Assembly Location

WL = Wafer Lot YY = Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

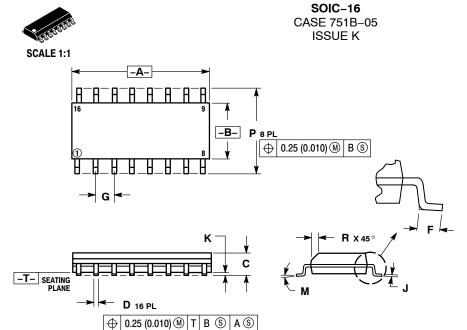
STYLE 1	:	STYLE 2	STYLE 2:		
PIN 1.	CATHODE	PIN 1.	COMMON DRAIN		
2.	CATHODE	2.	COMMON DRAIN		
3.	CATHODE	3.	COMMON DRAIN		
4.	CATHODE	4.	COMMON DRAIN		
5.	CATHODE	5.	COMMON DRAIN		
6.	CATHODE	6.	COMMON DRAIN		
7.	CATHODE	7.	COMMON DRAIN		
8.	CATHODE	8.	COMMON DRAIN		
9.	ANODE	9.	GATE		
10.	ANODE	10.	SOURCE		
11.	ANODE	11.	GATE		
12.	ANODE	12.	SOURCE		
13.	ANODE	13.	GATE		
14.	ANODE	14.	SOURCE		
15.	ANODE	15.	GATE		
16.	ANODE	16.	SOURCE		

SIDE VIEW

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MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.		PIN 1.		PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	E #1	
2.			ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR			8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.		11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.		12.			
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DEDING	FOOTPRINT
14.			NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDENING	FOOTFRINT
15.	EMITTER		ANODE	15.	EMITTER, #4	15.	BASE, #1	:	8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	6	.40
								-	0
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 ← ➤
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				,
2.	DRAIN. #1		CATHODE	2.	COMMON DRAIN (OUTPUT	1		. 🗀 1	16
3.	DRAIN, #2		CATHODE	3.	COMMON DRAIN (OUTPUT			↓ — ·	· · ·
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,		<u>-</u>	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	1	16	6X 🛣	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		0.9		' <u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT		0.	56	ı
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	•			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT)			V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	•			
	- /							□ 8	9 + - + -
									~
									DIMENSIONS: MILLIMETERS

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MECHANICAL CASE OUTLINE

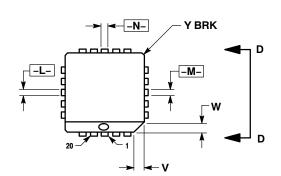


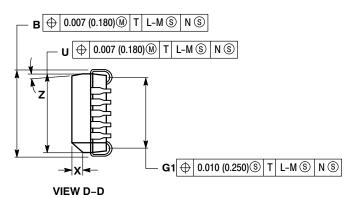


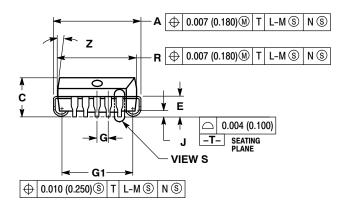
20 LEAD PLCC CASE 775-02 ISSUE G

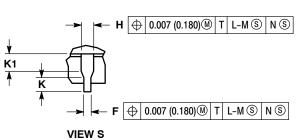
DATE 06 APR 2021











NOTES

- DIMENSIONS AND TOLERANCING PER ANSI Y14.5M,
- 2. DIMENSIONS IN INCHES.
- DATUMS -L-, -M-, AND -N- DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD

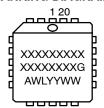
- PARTING LINE.
 DIMENSION GT, TRUE POSITION TO BE MEASURED AT DATUM -T -, SEATING PLANE.
 DIMENSIONS R AND U DO NOT INCLUDE MOLD FLASH.
 ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.
 DIMENSIONS IN THE PACKAGE TOP MAY BE SMALLER
 THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300).
 DIMENSIONS R AND U ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY
 EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE
 BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
- DIMENSION H DOES NOT INCLUDE DAMBAR
 PROTRUSION OR INTRUSION. THE DAMBAR
 PROTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

l .	INCHES		MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.385	0.395	9.78	10.03	
В	0.385	0.395	9.78	10.03	
С	0.165	0.180	4.20	4.57	
E	0.090	0.110	2.29	2.79	
F	0.013	0.021	0.33	0.53	
G	0.050	BSC	1.27	BSC	
Н	0.026	0.032	0.66	0.81	
J	0.020		0.51		
K	0.025		0.64		
R	0.350	0.356	8.89	9.04	
U	0.350	0.356	8.89	9.04	
V	0.042	0.048	1.07	1.21	
W	0.042	0.048	1.07	1.21	
Х	0.042	0.056	1.07	1.42	
Υ	-	0.020		0.50	
Z	2°	10 °	2 °	10 °	
G1	0.310	0.330	7.88	8.38	
K1	0.040		1.02		

INCHES

MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot = Year YY WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " = ", may or may not be present.

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